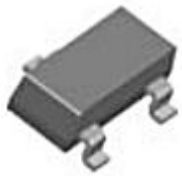
Data Sheet

NPN SILICON TRANSISTOR
AMPLIFIER TRANSISTOR

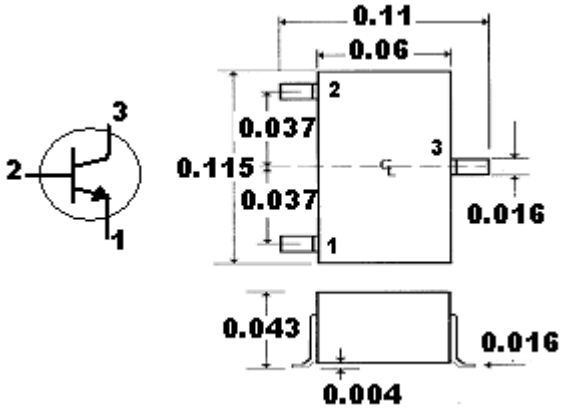
FMBTA06

Description



SOT-23

Mechanical Dimensions



Dimension in inchs

- ☐ JUNCTION TEMPERATURE ---------- +150℃ MAX
- ☐ STORAGE TEMPERATURE ---------- -55~ + 150℃
- ☐ MAX POWER DISSIPATION Ta=25℃ ---------- 250mW
- ☐ MAX VOLTAGE AND CURRENT Ta=25℃

  VCBO COLLECTOR TO BASE VOLTAGE---------- 80V

  VCEO COLLECTOR TO EMITTER VOLTAGE-------- 80V

  VEBO EMITTER TO BASE VOLTAGE---------- 4V

  IC COLLECTOR CURRENT---------- 500mA

Characteristics (Ta=25℃)

Collector-Emitter Voltage@ Ic=10mA	Vceo		80V
Collector-Base Breakdown@ Voltage Ic=100uA	Vcbo		80V
Emitter- base Breakdown Voltage@ Ie =100uA	Vebo		4V
Collector Cutoff Current@ Vcb=80V	Icbo	Max	100nA
mitter cutoff Current@ Vce=60V	Iceo	Max	100nA
Ic=100mA, Ib=10mA	Vce(sat)	Max	0.25V
Ic=100mA, Vce=1V	Vbe(on)	Max	1.2V
Static Forward Current Transfer Ratio			
Ic=10mA, Vce=1V	hFE1	Min	50
Ic=100mA, Vce=1V	hFE2	Min	50
Current-Gain-bandwidth Product			
@Ic=10mA, Vce=2V, f=100MHz	fT	Min	100MHz

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Characteristics Curve